



TMGN4060NF

N-Channel Enhancement Mosfet

General Description

- Low $R_{DS(ON)}$
- RoHS and Halogen-Free Compliant

Applications

- Load switch
- PWM

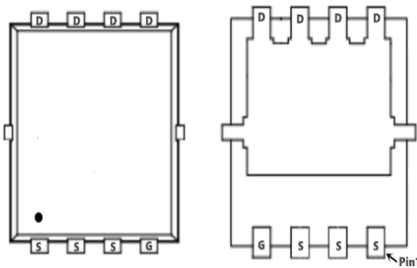
General Features

$V_{DS} = 40V$ $I_D = 60A$

$R_{DS(ON)} = 6.9m\Omega(\text{typ.})@V_{GS}=10V$

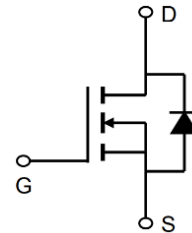
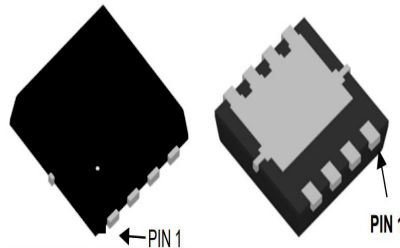
100% UIS Tested

100% R_g Tested



Marking: 60N04

NF:DFN5x6-8L



Absolute Maximum Ratings ($T_A=25^\circ\text{C}$ Unless Otherwise Noted)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	40	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D@T_C=25^\circ\text{C}$	Continuous Drain Current ¹	60	A
$I_D@T_C=100^\circ\text{C}$	Continuous Drain Current ¹	35	A
I_{DM}	Pulsed Drain Current ²	130	A
EAS	Single Pulse Avalanche Energy ³	48	mJ
I_{AS}	Avalanche Current	35	A
$P_D@T_C=25^\circ\text{C}$	Total Power Dissipation ⁴	39	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient (Steady State) ¹	---	60	$^\circ\text{C/W}$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	---	3.2	$^\circ\text{C/W}$

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Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250uA	40	---	---	V
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =10V, I _D =12A	---	6.9	8.5	mΩ
		V _{GS} =4.5V, I _D =10A	---	10.0	15	
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =250uA	1.35	---	3	V
I _{DSS}	Drain-Source Leakage Current	V _{DS} =32V, V _{GS} =0V, T _J =25°C	---	---	1	uA
		V _{DS} =32V, V _{GS} =0V, T _J =55°C	---	---	5	
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±20V, V _{DS} =0V	---	---	±100	nA
R _g	Gate Resistance	V _{DS} =0V, V _{GS} =0V, f=1MHz	---	1.7	---	Ω
Q _g	Total Gate Charge (4.5V)	V _{DS} =20V, V _{GS} =4.5V, I _D =12A	---	5.8	---	nC
Q _{gs}	Gate-Source Charge		---	3	---	
Q _{gd}	Gate-Drain Charge		---	1.2	---	
T _{d(on)}	Turn-On Delay Time	V _{DD} =15V, V _{GS} =10V, R _G =3.3Ω I _D =1A	---	14.3	---	ns
T _r	Rise Time		---	5.6	---	
T _{d(off)}	Turn-Off Delay Time		---	20	---	
T _f	Fall Time		---	11	---	
C _{iss}	Input Capacitance	V _{DS} =15V, V _{GS} =0V, f=1MHz	---	690	---	pF
C _{oss}	Output Capacitance		---	193	---	
C _{rss}	Reverse Transfer Capacitance		---	38	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I _s	Continuous Source Current ^{1,5}	V _G =V _D =0V, Force Current	---	---	60	A
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V, I _s =1A, T _J =25°C	---	---	1	V

Note :

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%
- 3.The EAS data shows Max. rating . The test condition is V_{DD}=25V,V_{GS}=10V,L=0.1mH,I_{AS}=31A
- 4.The power dissipation is limited by 150°C junction temperature
- 5.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

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Typical Characteristics

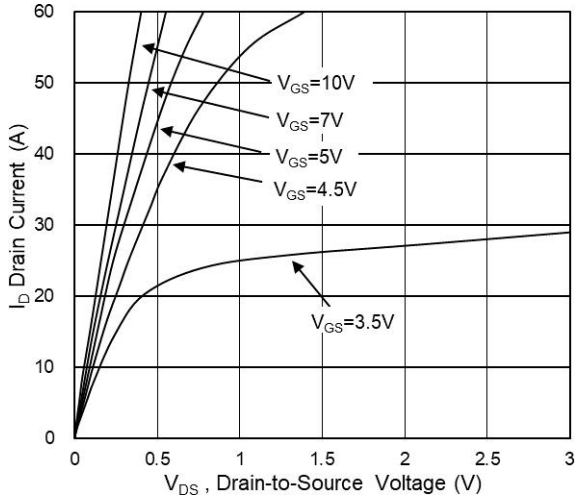


Fig.1 Typical Output Characteristics

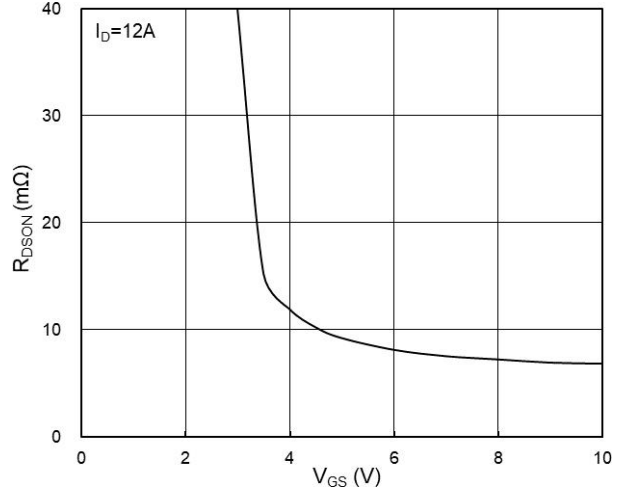


Fig.2 On-Resistance vs G-S Voltage

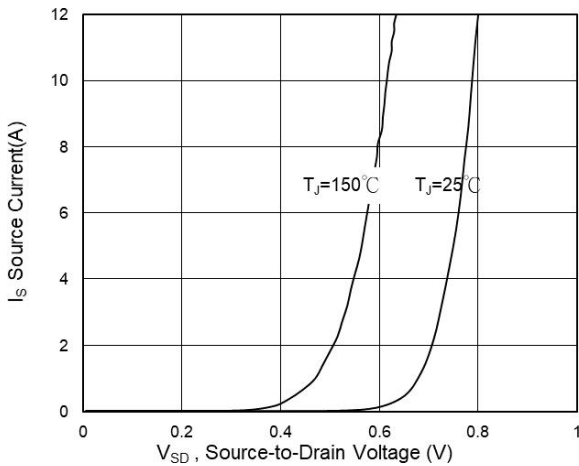


Fig.3 Source Drain Forward Characteristics

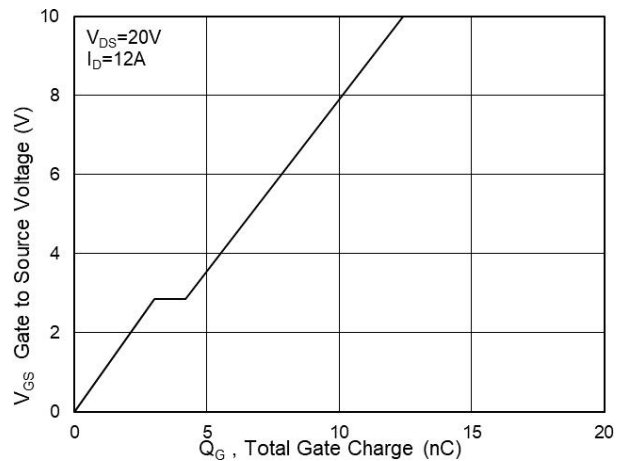


Fig.4 Gate-Charge Characteristics

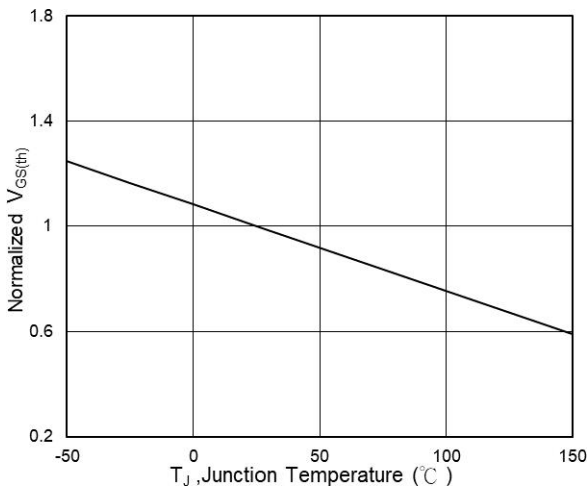


Fig.5 Normalized $V_{GS(th)}$ vs T_J

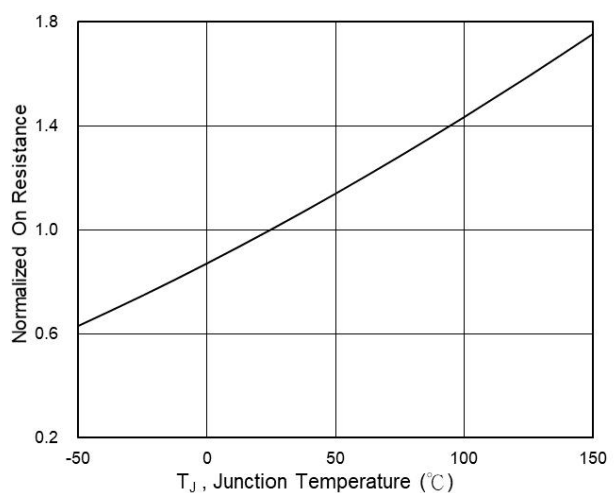


Fig.6 Normalized $R_{DS(on)}$ vs T_J

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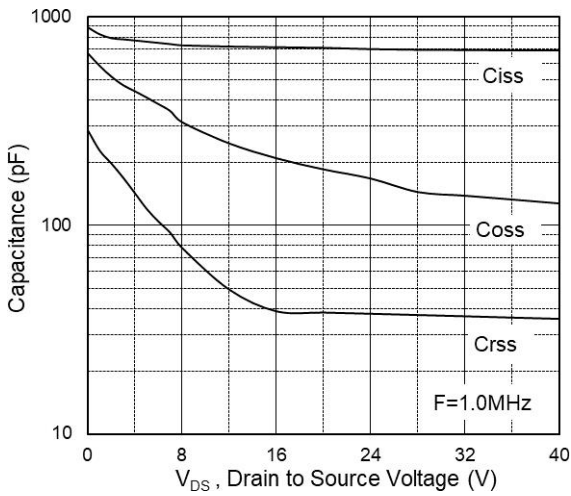


Fig.7 Capacitance

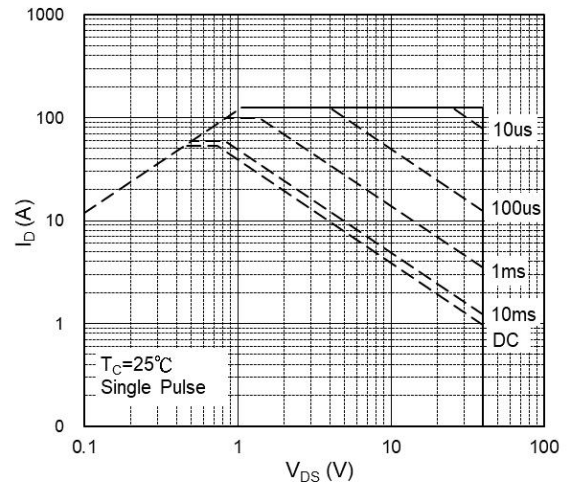


Fig.8 Safe Operating Area

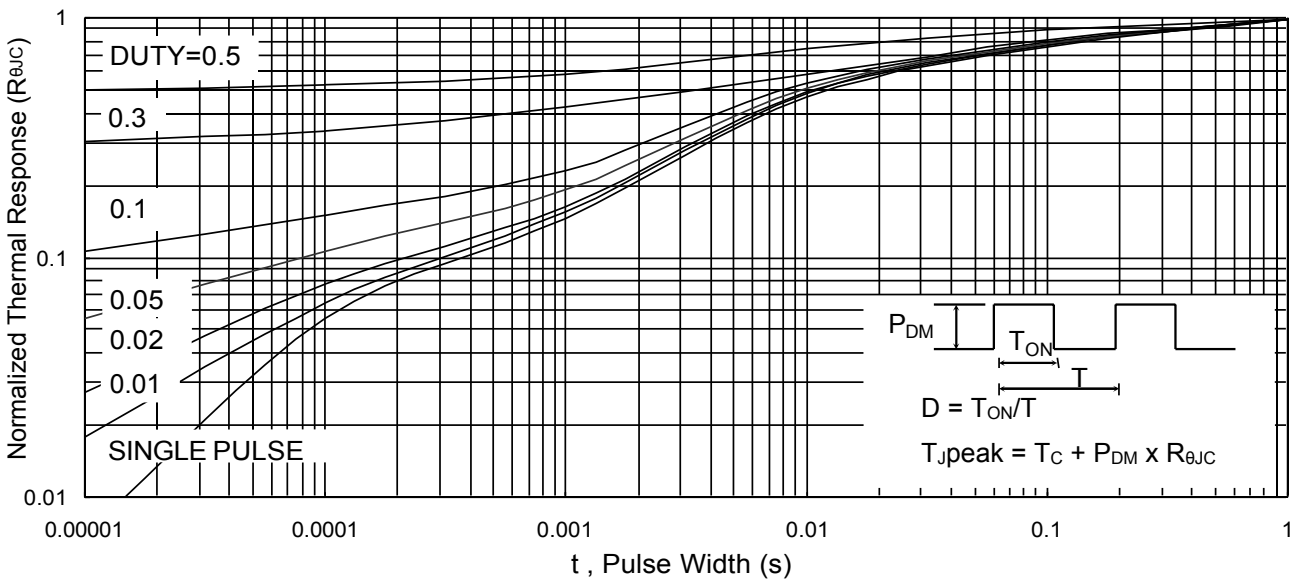


Fig.9 Normalized Maximum Transient Thermal Impedance

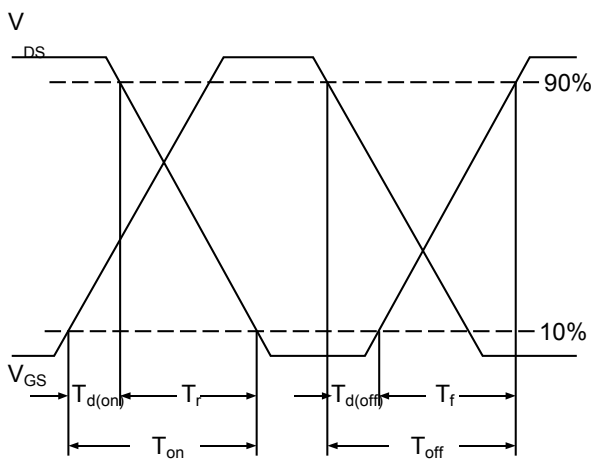


Fig.10 Switching Time Waveform

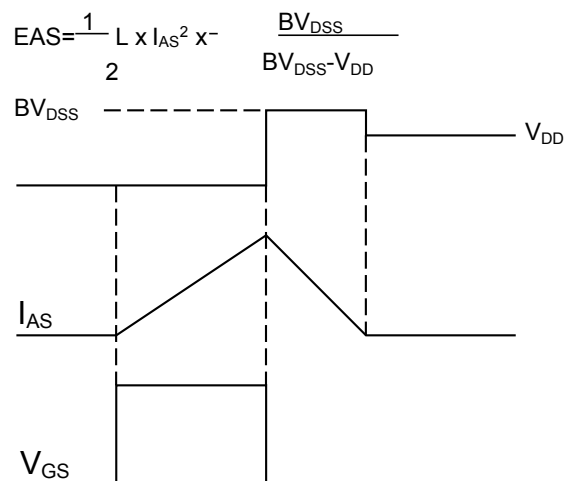
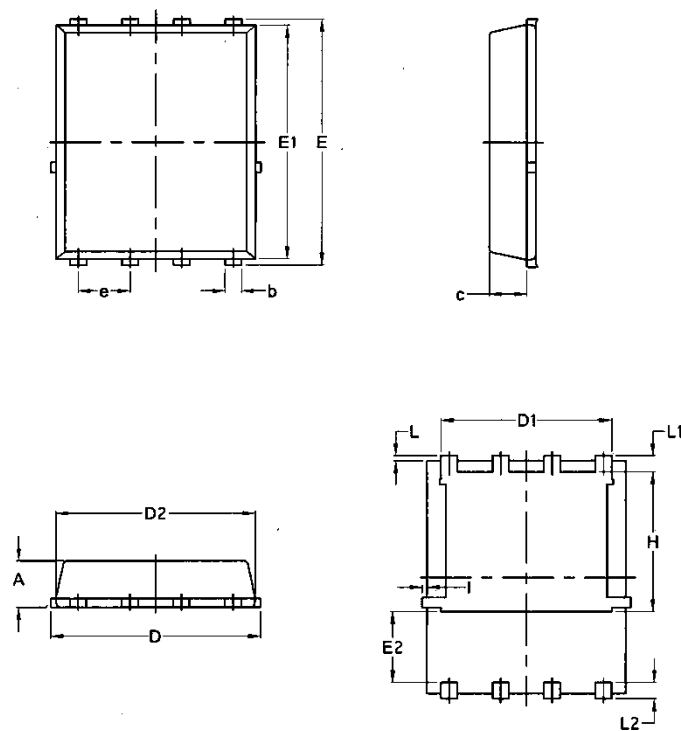


Fig.11 U clamped Inductive Waveform

Package Mechanical Data:DFN5x6-8L



Symbol	Common			
	mm		Inch	
	Min	Max	Min	Max
A	1.03	1.17	0.0406	0.0461
b	0.34	0.48	0.0134	0.0189
c	0.824	0.0970	0.0324	0.082
D	4.80	5.40	0.1890	0.2126
D1	4.11	4.31	0.1618	0.1697
D2	4.80	5.00	0.1890	0.1969
E	5.95	6.15	0.2343	0.2421
E1	5.65	5.85	0.2224	0.2303
E2	1.60	/	0.0630	/
e	1.27 BSC		0.05 BSC	
L	0.05	0.25	0.0020	0.0098
L1	0.38	0.50	0.0150	0.0197
L2	0.38	0.50	0.0150	0.0197
H	3.30	3.50	0.1299	0.1378
I	/	0.18	/	0.0070

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